


PTO-1449 REPRODUCED		ATTORNEY DOCKET NO. 3177.1000-000		APPLICATION NO. 09/863,013	
SUPPLEMENTAL INFORMATION DISCLOSURE CITATION IN AN APPLICATION				APPLICANT Milan R. Kokta et al.	
January 29, 2003 (Use several sheets if necessary)				FILING DATE May 22, 2001	
				CONFIRMATION NO. 7269	
				GROUP 2828	
U.S. PATENT DOCUMENTS					
EXAM- INER INI- TIAL		DOCUMENT NUMBER	ISSUE DATE / PUBLICATION DATE	NAME	
H✓	AC	3,655,439	04/11/72	Seiter	
H✓	AD	3,658,586	04/25/72	Wang	
H✓	AE	3,796,597	03/12/74	Porter, et al.	
H✓	AF	4,177,321	12/04/79	Nishizawa	
H✓	AG	5,741,724	04/21/98	Ramdani, et al.	
H✓	AH	5,850,410	12/15/98	Kuramata	
	AI				
FOREIGN PATENT DOCUMENTS					
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS
	AL				
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
H✓	AZ	Tsuchiya, T., et al., "Epitaxial growth of InN films on MgAl ₂ O ₄ (1 1 1) substrates," J. of Crystal Growth 220:185-190 (2000). <i>no months</i>			
H✓	AR2	Efimov, A.N., et al., "On an Unusual Azimuthal Orientation Relationship in the System Gallium Nitride Layer on Spinel Substrate," Crystallography Reports, 45(2):312-317 (2000). <i>no months</i>			
H✓	AS2	Yang, H.F., et al., "Microstructure evolution of GaN buffer layer on MgAl ₂ O ₄ substrate," J. of Crystal Growth 193:478-483 (1998). <i>no months</i>			
H✓	AT2	Ohsato, H., et al., "Epitaxial orientation and a growth model of (0 0 1) GaN thin film on (1 1 1) spinel substrate," J. of Crystal Growth 189/190:202-207 (1998). <i>no months</i>			
H✓	AU2	Duan, S., et al., "MOVPE growth of GaN and LED on (1 1 1) MgAl ₂ O ₄ ," J. of Crystal Growth 189/190:197-201 (1998). <i>no months</i>			
H✓	AV2	Nikishin, S.A., et al., "Gas source molecular beam epitaxy of GaN with hydrazine on spinel substrates," App. Phys. Lett. 72(19):2361-2363 (1998).			
H✓	AW2	Sun, C.J., et al., "Mg-doped green light emitting diodes over cubic (1 1 1) MgAl ₂ O ₄ substrates," App. Phys. Lett. 70(11):1444-1446 (1997) <i>no months</i>			
H✓	AX2	Efimov, A.N., et al., "Symmetry constraints and epitaxial growth on non-isomorphic substrate," Thin Solid Films 260:111-117 (1995). <i>no months</i>			
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
AY2	Kruger, M.B., et al., "Equation of state of $MgAl_2O_4$ spinel to 65 GPa," <i>Physical Review B Condensed Matter, Third Series</i> 56(1):1-4 (1997). <i>no months</i>				
AZ2	George, T., et al., "Novel symmetry in the growth of gallium nitride on magnesium aluminate substrates," <i>Appl. Phys. Lett.</i> 68(3):337-339 (1996). <i>no months</i>				
AR3	Sun, C.J., et al., "Deposition of high quality wurtzite GaN films over cubic (1 1 1) $MgAl_2O_4$ substrates using low pressure and metalorganic chemical vapor deposition," <i>Appl. Phys. Lett.</i> 68(8):1129-1131 (1996). <i>no months</i>				
AS3	Nakamura, S., et al., "Characteristics of InGaN multi-quantum-well-structure laser diodes," <i>Appl. Phys. Lett.</i> 68(23):3269-3271 (1996). <i>no months</i>				
AT3	Kuramata, A., et al., "Properties of GaN Epitaxial Layer Grown on (1 1 1) $MgAl_2O_4$ Substrate," <i>Solid-State Electronics</i> 41(2):251-254 (1997). <i>no months</i>				
AU3	Khan, M.A., et al., "Cleaved cavity optically pumped InGaN-GaN laser grown on spinel substrates," <i>Appl. Phys. Lett.</i> 69(16):2418-2420 (1996). <i>no months</i>				
AV3	Tempel, A. and Seifert, W., "Nachweis von Stapelfehlern in GaN-Exitaxieschichten mittels Elektronenbeugung," <i>Kristall und Technik</i> 10(7):741-746 (1975). <i>no months</i>				
AW3	Gritsyna, V.T., et al., "Structure and Electronic States of Defects in Spinel of Different Compositions $MgO \cdot nAl_2O_3 \cdot Me$," <i>J. Am. Ceram. Soc.</i> 82(12):3365-3373 (1999). <i>no months</i>				
AX3	Tempel, A., et al., "Zur Epitaxie von Galliumnitrid auf nichtstöchiometrischem Spinell im System $GaCl/NH_3/He$," <i>Kristall und Technik</i> 10(7):747-758 (1975). <i>no months</i>				
AY3	E. Hellman, "Exotic and Mundane Substrates for Gallium Nitride Heteroepitaxy," Bell Laboratories/Lucent Technologies (no date given). <i>no months</i>				
AZ3	Sheldon, R.I., et al., "Cation Disorder and Vacancy Distribution in Nonstoichiometric Magnesium Aluminate Spinel, $MgO \cdot xAl_2O_3$," <i>J. Am Ceram. Soc.</i> 82(12):3293-3298 (1999). <i>no months</i>				
AR4	K.V. Yumashev, "Saturable absorber $Co^{2+}:MgAl_2O_4$ crystal for Q switching of 1.34- μm $Nd^{3+}:YAlO_3$ and 1.54- μm Er^{3+} :glass lasers," <i>Applied Optics</i> 38(30):6343-6346 (1999). <i>no months</i>				
AS4	T.E. Mitchell, "Dislocations and Mechanical Properties of $MgO-Al_2O_3$ Spinel Single Crystals," <i>J. Am. Ceram. Soc.</i> 82(12):3305-3316 (1999). <i>no months</i>				
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